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cont.

wafer 23. In this case, the infrared source 74 and the infrared camera 75 may be moved or shifted along a horizontal direction in unison.

IN THE CLAIMS:

Please CANCEL claims 5 and 7 without prejudice or disclaimer.

Please AMEND claims 6, 8 and 9 and ADD new claims 29 and 30 in accordance with the following:

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6. (Amended) A method of making a semiconductor chip, comprising:
forming a conductive bump on an upward front side of a wafer;
reversing the wafer; and
transferring a resin sheet, adhered to a surface of a thin film member, to a backside of the wafer, so as to form a resin lamination on the backside of the wafer.

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8. (Amended) A method of making a semiconductor chip, comprising:
reversing a wafer receiving a conductive bump on an upward front side;
irradiating an X-ray on the wafer;
determining a cutting position on the wafer based on the X-ray penetrating through the wafer; and
dicing the wafer from a backside of the wafer based on the cutting position.

9. (Amended) The method of making according to claim 8, further comprising:
forming a nick along a contour of the semiconductor chip on the backside of the wafer;
and
forming an evaporated resin lamination on the backside of the wafer.